## Co-Research

## **Research Entrusted by National Government and Public Institute**

- Core Research for Evolutionary Science and Technology Project (CREST) of Japan Science and Technology Agency (JST)
   Theme: Spin Measurement
   Project Number: JPMJCR9538
   Principal Researcher: Prof. Kouichi Mukasa of Faculty of Engineering, Hokkaido University
   My Role: Research Advisor
   Budget: ¥ 800 M
   Period: Apr. 1, 1997 to Mar. 31, 2001
- Grant-in-Aid for Scientific Research B of Japan Society for the Promotion of Science (JSPS) Issue number: 16360008

Theme: Analysis of Degradation Mechanism in Light-Emitting Devices of II-VI and III-V Wide-Gap Semiconductors and its Control

Project Number: 16360008

Principal Researcher: Prof. Koshi Ando of Tottori University

My Role: Collaboration Researcher

Budget: ¥ 11.3 M

Period: Apr.1, 2004 to Mar. 31, 2007

3. Core Research for Evolutionary Science and Technology Project (CREST) of Japan Science and Technology Agency (JST)

Specific Research Investigation: Nano Light-Emitting-Materials Research and their Device Fabrication Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Budget: ¥ 5 M Period: Oct. 1, 2005 to Mar. 31, 2006

4. Grant-in-Aid for Research on Creation of Functional Nanomaterials in Institute for Materials Research (IMR), Tohoku University

Theme: Nano Light-Emitting-Materials Research and their Device Fabrication Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research, Tohoku University Budget: ¥ 10 M Period: Apr. 1, 2006 to Mar. 31, 2008  Core Research for Evolutionary Science and Technology Project (CREST) of Research Area "Photonics and Quantum Optics for the Creation of Innovative Functions", Japan Science and Technology Agency (JST)

Theme: Research on InN Semiconductor Lasers with High Temperature-Stability for Optical Communications Systems

Project Number: JPMJCR06J48 Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Budget: ¥ 410 M Period: Oct. 1, 2006 to Mar. 31, 2012

- 6. Grant-in-Aid for Research of Iwate Industrial Research Institute Theme: Research on Fabrication of Nitride Thin Films with MOVPE and their Evaluation Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Budget: ¥ 1 M Period: Jan. 1, 2006 to Mar. 31, 2006
- 7. Grant-in-Aid for Commercialization-Feasibility Test of Research Plaza Miyagi, Japan Science and Technology Agency (JST)

Theme: Establishment of Thin Film Fabrication Technology of High Quality InGaN Lattice-Matching to ZnO Substrate for Blue-Emitter

Project Number: JST-PROJECT-7700009413

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Budget: ¥ 2 M

Period: Oct. 1, 2006 to Feb. 28, 2007

 2009 Developmental Scientific Research A on Seeds Discover, Japan Science and Technology Agency (JST)
 Theme: Development of "Elemental Technology" for Nitride-Semiconductor Solar Cells with Super High Efficiency

Project Number: JST-PROJECT-09157817

Principal Researcher: Assistant Professor Yuhuai Liu of Institute for Materials Research (IMR), Tohoku University My Role: Advisor

Budget:  $\ge 2 M$ 

Period: Apr. 1, 2009 to Mar. 31, 2010

9. 2009 Developmental Scientific Research B (Expansion) on Seeds Discover, Japan Science and Technology Agency (JST)

Theme: Establishment of High-Temperature Growth Technique of Green-Light-Emitting InGaN on ZNO Substrate with MOVPE

Project Number: JST-PROJECT-09157896 Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Budget: ¥ 5 M Period: Apr. 1, 2009 to Mar. 31, 2010

- 10. Core Research for Evolutionary Science and Technology Project (CREST) of Research Area "Creative Research for Clean Energy Generation using Solar Energy", Japan Science and Technology Agency (JST)
  Theme: High Efficiency Thin Film Solar Cells with Enhanced Optical Absorption by Excitons
  Project Number: JPMJCR09Q6
  Principal Researcher: Prof. Yoshiji Horikoshi of School of Advanced Science and Engineering, Waseda University
  My Role: Vice Principal Researcher
  Budget: ¥ 242.79 M
  Period: Oct. 1, 2006 to Mar. 31, 2015
- 11. Grant-in-Aid for Scientific Research C of Japan Society for the Promotion of Science (JSPS)
  Theme: Development of Red-Light-Emitting Layer Consisted of Nitride Semiconductor for Monolithic White Light Source
  Project Number: 23560356
  Principal Researcher: Assistant Professor Yuhuai Liu of Institute for Materials Research (IMR), Tohoku University My Role: Advisor

Budget: ¥ 4.1 M Period: Apr.1, 2011 to Mar. 31, 2013

 Adaptable and Seamless Technology Transfer Program through Target Driven R&D (A-Step), Feasibility Study Stage: Investigation-Type of Japan Science and Technology Agency (JST) Theme: Research and Development of "Elemental Technology" for Nitride-Semiconductor Solar Cells with Super High Efficiency on Si Substrate Project Number: JST-PROJECT-1110454 Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University

Budget: ¥ 1.7 M

Period: Dec. 1, 2011 to July 31, 2012

 Grant-in-Aid for Scientific Research C of Japan Society for the Promotion of Science (JSPS) Project Number: 24560362

Theme: Development of Red-Light-Emitting Layer for Realizing White Light Source Consisted of Only Nitride Semiconductors

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Budget: ¥ 4.98 M

Period: Apr.1, 2012 to Mar. 31, 2015

14. Reconstruction Promotion Program A-STEP, Investigation-Type of Japan Science and Technology Agency (JST) Theme: Research on Quality Improvement of Epitaxially Grown GaN by Introducing Lattice-Matching ScAlMgO4 Substrate

Project Number: JST-PROJECT-12101475

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Budget: ¥ 2.99 M Pariad: Oat 1, 2012 to Sant 30, 2013

Period: Oct. 1, 2012 to Sept. 30, 2013

- Adaptable and Seamless Technology Transfer Program through Target Driven R&D (A-Step), Feasibility Study Stage: Investigation-Type of Japan Science and Technology Agency (JST)
  - Theme: Practical Research on Epitaxial Growth of Indium-Rich InAlN for Device Applications of Nitride Semiconductors
  - Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Budget: ¥ 1.7 M

Period: Aug. 1, 2013 to Mar. 31, 2014

16. 2014 Research Program on Creation of Base Materials for Realization of Low-Carbon Society of Institute for Materials Research (IMR), Tohoku University
Theme: Application of N-Polar InAlN Compound Semiconductors Grown with Low- and High-Pressure Metalorganic Vapor Phase Epitaxial Growth for High-Efficient Opt-Electronic Devices
Principal Researcher: Assist. Prof. Shigeyuki Kuboya of Institute for Materials Research (IMR), Tohoku University
My Role: Advisor
Budget: ¥ 4 M

Period: Apr. 1, 2014 to Mar. 31, 2016

17. Grant-in-Aid for Challenging Exploratory Research of Japan Society for the Promotion of Science (JSPS)

Theme: Research on Fabrication Process of Vertical-Type Transistors consisted of Nitride Semiconductors on ScAlMgO<sub>4</sub> substrate
Project Number: 15K13963
Principal Researcher: Prof. Tetsuya Suemitsu of Research Institute of Electrical Communications (RIEC), Tohoku University
My Role: Collaboration Researcher
Budget: ¥ 3.9 M
Period: Apr.1, 2015 to Mar. 31, 2017

- 18. 2015 Contributing to Society by Accelerating Innovation and Achieving Results in a Timely Manner of New Energy and Industrial Technology Development Organization (NEDO)
  Theme: Development of GaN-Based Substrate for LED with High Efficiency and Low Cost Type E/Practical Development Phase
  Principal Research Company: Panasonic Corporation
  My Role: Collaboration Researcher
  Budget: ¥ 405 M
  Period: Aug. 1, 2015 to Mar. 31, 2018
- 19. Grant-in-Aid for Scientific Research B of Japan Society for the Promotion of Science (JSPS)
  Project Number: 16H04341
  Theme: Growth Technique of Structure Generating Two-Dimensional Electron Gas by Nitride Semiconductors
  Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University
  Budget: ¥ 16.25 M
  Period: Apr.1, 2016 to Mar. 31, 2018

20. Grant-in-Aid for Scientific Research B of Japan Society for the Promotion of Science (JSPS)
Project Number: 16H04221
Theme: Asymmetric-Waveguide-Coupled Multi-Striped Orthogonal Photo-Photocarrier-Propagation Solar Cell
Principal Researcher: Prof. Akira Ishibashi of Research Institute for Electronic Science (RIES), Hokkaido University
My Role: Co-Investigator
Budget: ¥ 16.12M
Period: Apr.1, 2016 to Mar. 31, 2019

21. Grant-in-Aid for Scientific Research B of Japan Society for the Promotion of Science (JSPS)
Theme: Crystal Growth of N-polar Nitride Semiconductor Heterostructures with Two-Dimensional Electron Gas
Project Number: 16H03857
Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University
Budget: ¥ 12.5 M
Period: Apr.1, 2016 to Mar. 31, 2019

22. Outsourcing Research of Tohoku University Theme: Research on Fabrication of Free-Standing GaN Wafer with Threading Dislocation less than 10<sup>5</sup>/cm<sup>2</sup> with HVPE Growth"

Principal Researcher: Małgorzata Iwińska of Institute of High Pressure Physics (Unipress),

Polish Academy of Science

My Role: Collaborate Researcher and Advisor

Period: Oct. 1, 2022 to Mar. 31, 2024

## **Collaboration with Private Companies**

1. Company A

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Period: Nov.24, 2005~Mar. 31, 2010 Budget: ¥ 23.05 M

2. Company B

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Period: Sept. 1, 2005~Mar. 31, 2009 Budget: ¥ 7 M

3. Company C

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Period: Jun. 28, 2011~Mar. 23, 2012 Budget: Nothing

4. Company D

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Period: Feb. 8, 2013~Mar. 31, 2018 Budget: Nothing

5. Company E

Principal Researcher: Lecturer Tomoyuki Tanikawa of Institute for Materials Research (IMR), Tohoku University

My role: Collaborator Period: Apr. 1, 2013~Mar. 31, 2019 Budget: ¥ 3 M

6. Company F

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University 1<sup>st</sup> Period

Period: Apr. 1, 2015~Mar. 31, 2017

Budget: ¥ 33.619

2<sup>nd</sup> Period

Period: Apr. 1, 2017~Mar. 31, 2019 Budget: ¥ 59.702 M

3rd Period

Period: Apr.1, 2021~Mar. 31, 2023

Budget: ¥ 52.81 M

## 7. Company G

Principal Researcher: Prof. Takashi Matsuoka of Institute for Materials Research (IMR), Tohoku University Period: Jul. 1, 2021~Jun. 30, 2023 Budget: ¥ 10.4 M

Engineering Guidance

Company H: Apr. 1, 2020~Mar. 31, 2022

Company I: Jul. 1, 2021~Jun. 30, 2022